Supplement Information

The Effect of Insulating Oxide Overlayers on Electron Injection Dynamics in Dye-Sensitized Nanocrystalline Thin Films

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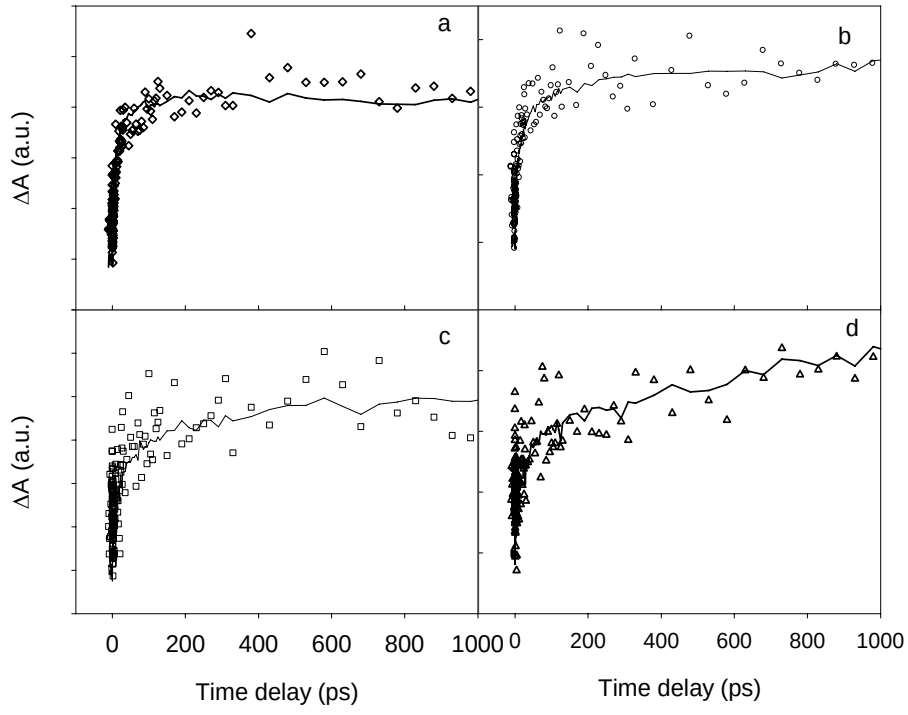

Figure S1. Comparison of the growth kinetics of injected electron absorption (solid line, averaged value from 2120 to 2150 cm^{-1}) and oxidized peak (symbols, integrated

peak area from 2076 to 2110 cm^{-1}) for ReC1P on TiO_2 with (a) 0, (b) 1, (c) 2, and (d) 3 over-layers of Al_2O_3. The injected electron and oxidized dye signals agree well at all time delays, indicating that either one can be used to monitor the electron transfer dynamics.